DIM600DDS12-A000

Dual Switch IGBT Module

Replaces DS5868-4

DS5868-5 October 2016 (LN33938)

FEATURES

- 10µs Short Circuit Withstand
- Non Punch Through Silicon
- Isolated Cu Base with Al_2O_3 Substrates
- Lead Free construction

APPLICATIONS

- High Reliability Inverters
- Motor Controllers

The Powerline range of high power modules includes half bridge, chopper, dual, single and bi-directional switch configurations covering voltages from 600V to 3300V and currents up to 2400A.

The DIM600DDS12-A000 is a dual switch 1200V, n-channel enhancement mode, insulated gate bipolar transistor (IGBT) module. The IGBT has a wide reverse bias safe operating area (RBSOA) plus 10µs short circuit withstand. This device is optimised for traction drives and other applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DIM600DDS12-A000

Note: When ordering, please use the complete part number

KEY PARAMETERS

V_{CES}		**1200V**
$V_{CE(sat)}$ *	**(typ)**	**2.2 V**
I_C	**(max)**	**600A**
$I_{C(PK)}$	**(max)**	**1200A**

* Measured at the power busbars, not the auxiliary terminals

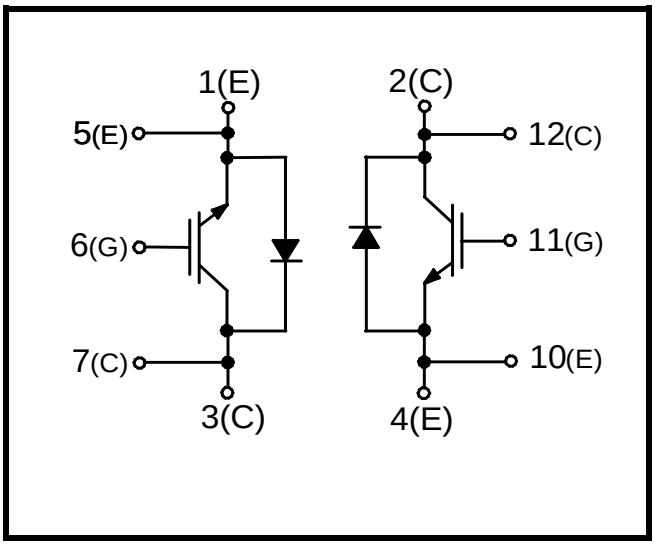
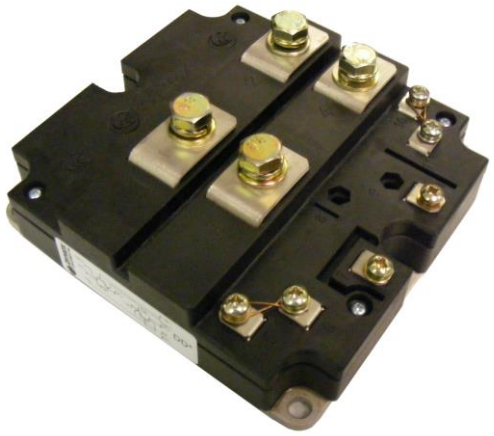


Fig. 1 Circuit configuration



Outline type code: D

(See Fig. 11 for further information)

Fig. 2 Package

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V_{CES}	Collector-emitter voltage	V_{GE} = 0V	1200	V
V_{GES}	Gate-emitter voltage		±20	V
I_C	Continuous collector current	T_{case} = 85°C	600	A
$I_{C(PK)}$	Peak collector current	1ms, T_{case} = 115°C	1200	A
P_{max}	Max. transistor power dissipation	T_{case} = 25°C, T_j = 150°C	5208	W
I^2t	Diode I^2t value	V_R = 0, t_p = 10ms, T_j = 125°C	100	kA^2s
V_{isol}	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	2500	V

THERMAL AND MECHANICAL RATINGS

Internal insulation material: Al_2O_3

Baseplate material: Cu

Creepage distance: 20mm

Clearance: 10mm

CTI (Comparative Tracking Index): >600

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$R_{th(j-c)}$	Thermal resistance – transistor (per switch)	Continuous dissipation - junction to case	-	-	24	°C/kW
$R_{th(j-c)}$	Thermal resistance – diode (per switch)	Continuous dissipation - junction to case	-	-	40	°C/kW
$R_{th(c-h)}$	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	8	°C/kW
T_j	Junction temperature	Transistor	-	-	150	°C
		Diode	-	-	125	°C
T_{stg}	Storage temperature range	-	-40	-	125	°C
	Screw torque	Mounting – M6	-	-	5	Nm
		Electrical connections – M4	-	-	2	Nm
		Electrical connections – M8	-	-	10	Nm

ELECTRICAL CHARACTERISTICS

T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I_{CES}	Collector cut-off current	V_{GE} = 0V, V_{CE} = V_{CES}			1	mA
		V_{GE} = 0V, V_{CE} = V_{CES}, T_{case} = 125°C			18	mA
I_{GES}	Gate leakage current	V_{GE} = ± 20V, V_{CE} = 0V			3	µA
$V_{GE(TH)}$	Gate threshold voltage	I_C = 20mA, V_{GE} = V_{CE}	4.5	5.5	6.5	V
$V_{CE(sat)}$	Collector-emitter saturation voltage	V_{GE} = 15V, I_C = 600A		2.2	2.8	V
		V_{GE} = 15V, I_C = 600A, T_j = 125°C		2.6	3.2	V
I_F	Diode forward current	DC			600	A
I_{FM}	Diode maximum forward current	t_p = 1ms			1200	A
V_F	Diode forward voltage	I_F = 600A		2.1	2.4	V
		I_F = 600A, T_j = 125°C		2.1	2.4	V
C_{ies}	Input capacitance	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		70		nF
Q_g	Gate charge	±15V		6		µC
C_{res}	Reverse transfer capacitance	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz				nF
L_M	Module inductance – per switch			20		nH
R_{INT}	Internal transistor resistance – per switch			270		µΩ
SC_{Data}	Short circuit current, I_{SC}	T_j = 125°C, V_{CC} = 900V t_p ≤ 10µs, V_{GE} ≤ 15V $V_{CE\ (max)}$ = V_{CES} – L* x dI/dt IEC 60747-9		3400		A

Note:
* L is the circuit inductance + L_M

ELECTRICAL CHARACTERISTICS

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$t_{d(off)}$	Turn-off delay time	I_C = 600A V_{GE} = ±15V V_{CE} = 600V $R_{G(ON)}$ = 2.7Ω $R_{G(OFF)}$ = 2.7Ω L_S ~ 120nH		920		ns
t_f	Fall time			140		ns
E_{OFF}	Turn-off energy loss			100		mJ
$t_{d(on)}$	Turn-on delay time			390		ns
t_r	Rise time			180		ns
E_{ON}	Turn-on energy loss			55		mJ
Q_{rr}	Diode reverse recovery charge	I_F = 600A V_{CE} = 600V dI_F/dt = 3600A/µs		100		µC
I_{rr}	Diode reverse recovery current			370		A
E_{rec}	Diode reverse recovery energy			50		mJ

T_{case} = 125°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$t_{d(off)}$	Turn-off delay time	I_C = 600A V_{GE} = ±15V V_{CE} = 600V $R_{G(ON)}$ = 2.7Ω $R_{G(OFF)}$ = 2.7Ω L_S ~ 120nH		1000		ns
t_f	Fall time			160		ns
E_{OFF}	Turn-off energy loss			125		mJ
$t_{d(on)}$	Turn-on delay time			460		ns
t_r	Rise time			180		ns
E_{ON}	Turn-on energy loss			65		mJ
Q_{rr}	Diode reverse recovery charge	I_F = 600A V_{CE} = 600V dI_F/dt = 3600A/µs		200		µC
I_{rr}	Diode reverse recovery current			480		A
E_{rec}	Diode reverse recovery energy			100		mJ

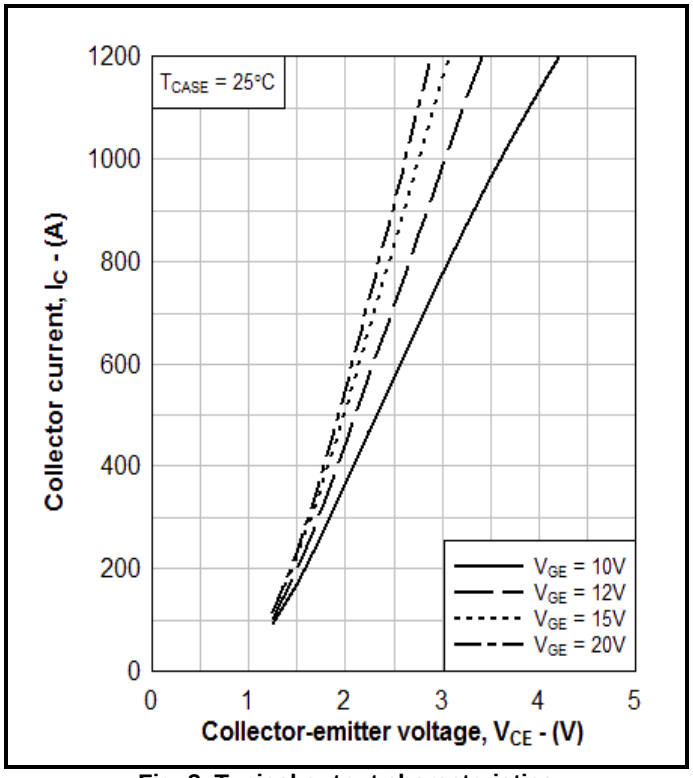


Fig. 3 Typical output characteristics

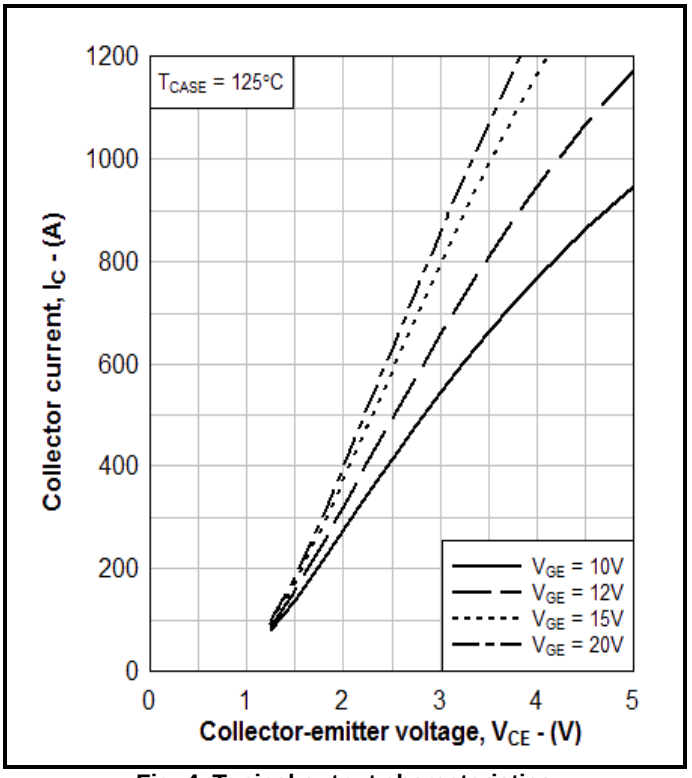


Fig. 4 Typical output characteristics

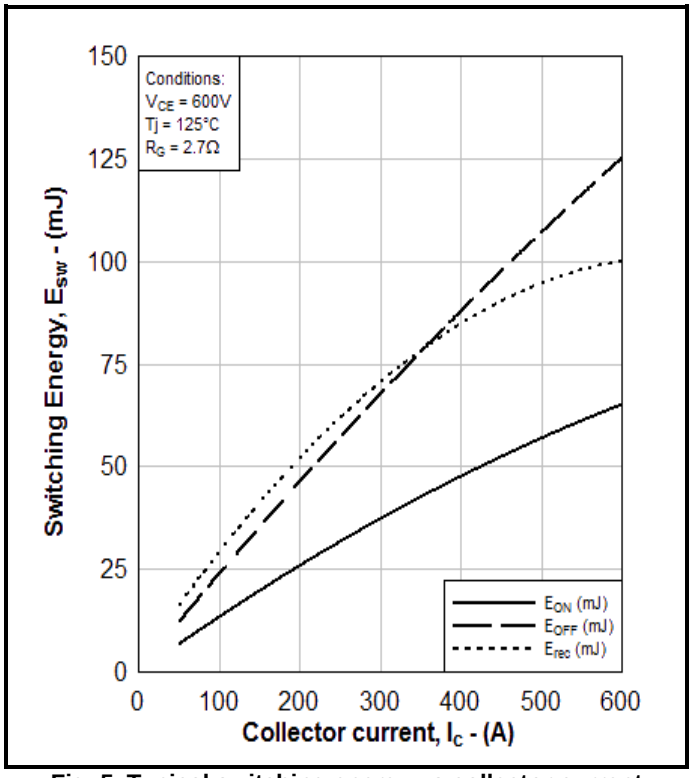


Fig. 5 Typical switching energy vs collector current

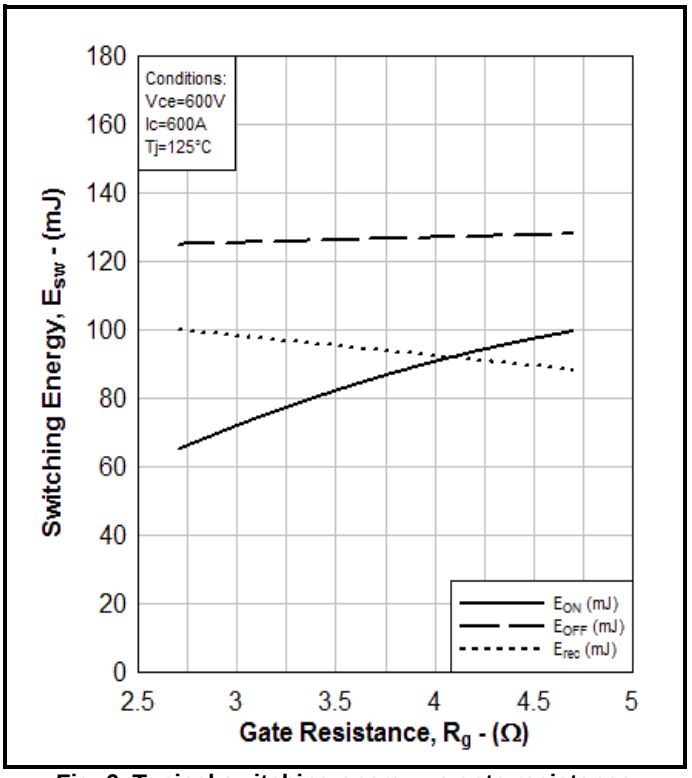


Fig. 6 Typical switching energy vs gate resistance

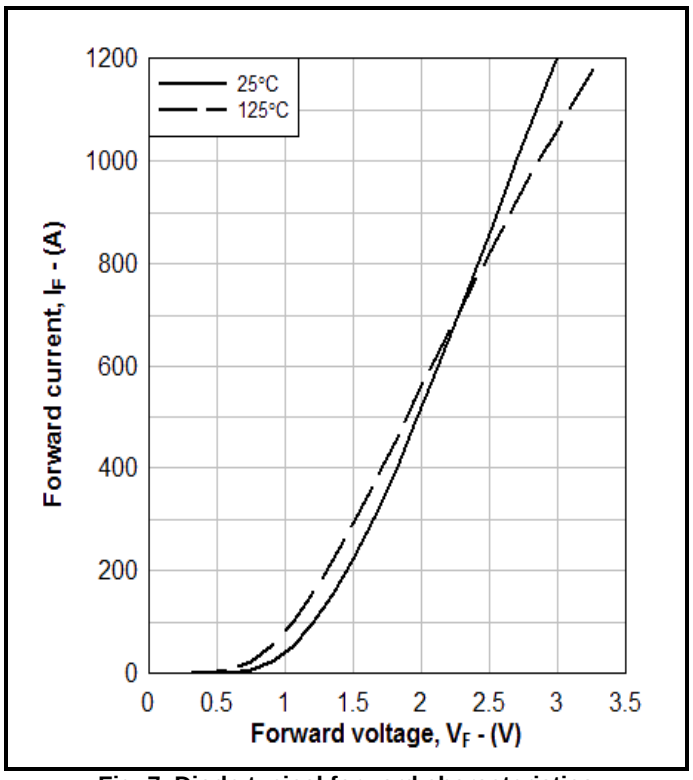


Fig. 7 Diode typical forward characteristics

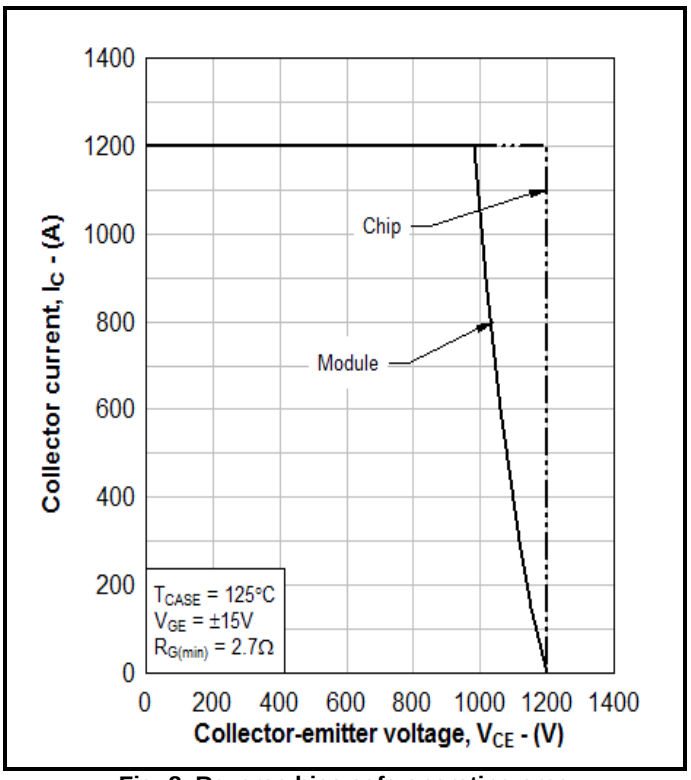


Fig. 8 Reverse bias safe operating area

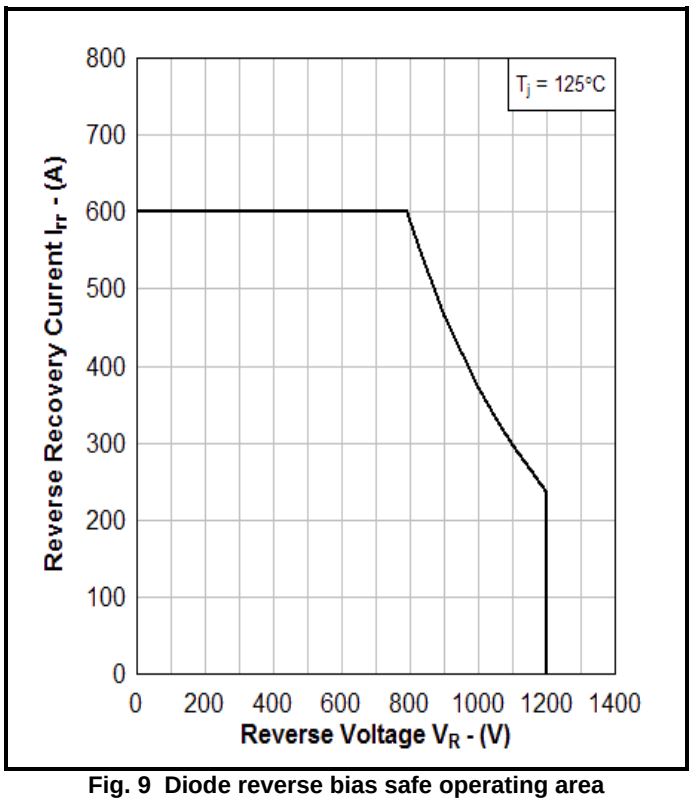


Fig. 9 Diode reverse bias safe operating area

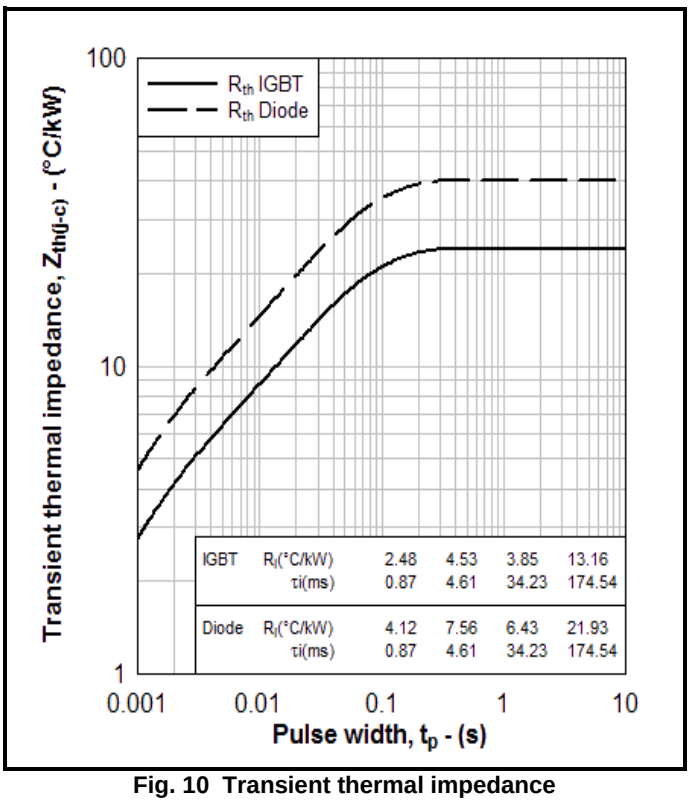
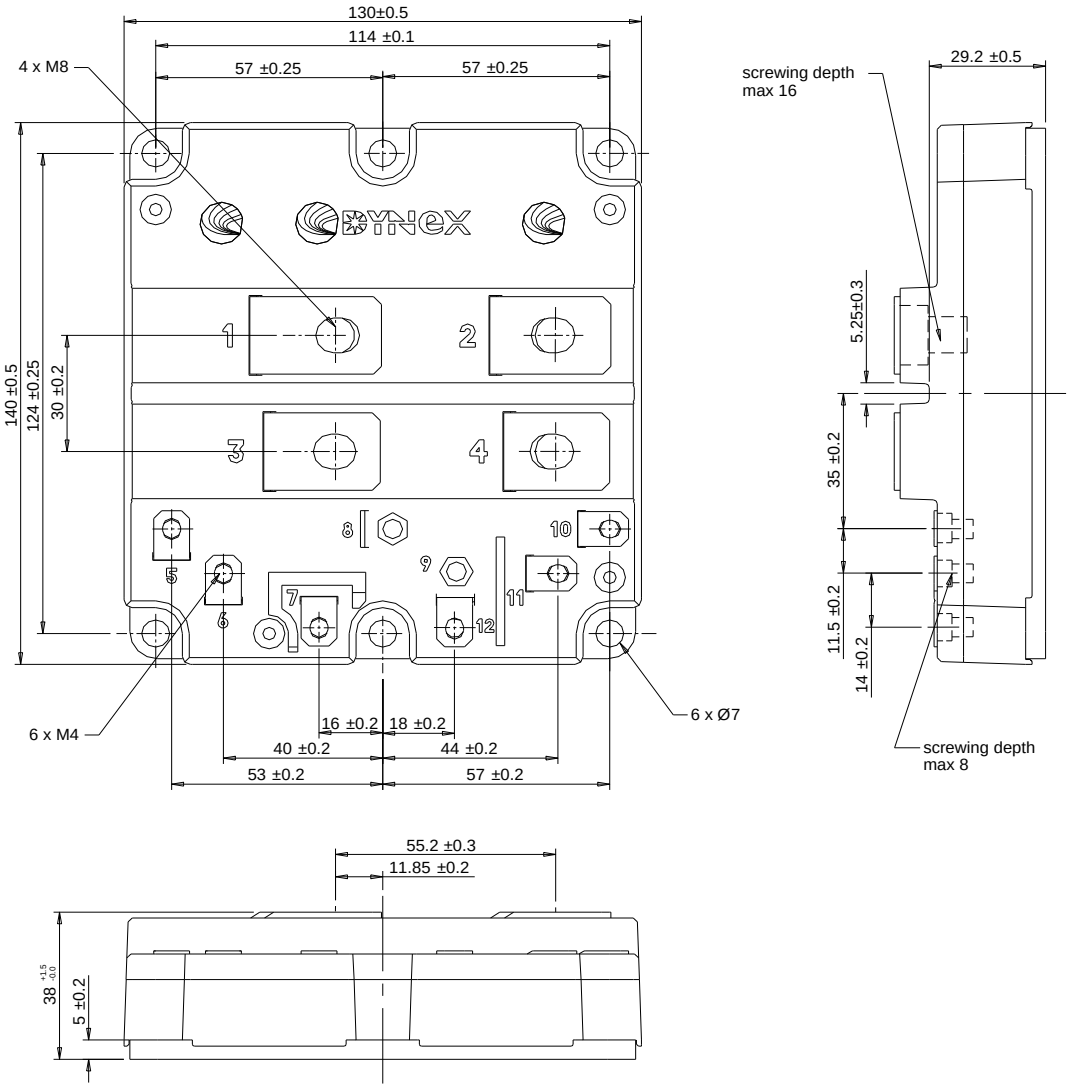


Fig. 10 Transient thermal impedance

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services.
All dimensions in mm, unless stated otherwise.
DO NOT SCALE.



Nominal Weight: 1450g

Module Outline Type Code: D

Fig. 11 Module outline drawing

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Caution: This device is sensitive to electrostatic discharge. Users should follow ESD handling procedures.